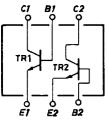


NPN Epitaxial Planar Silicon Composite Transistor High-Frequency General-Purpose Amp, Differential Amp Applications

Features

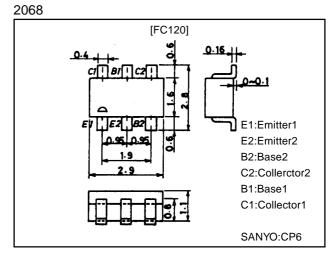
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC120 is formed with two chips, being equivalent to the 2SC3142, placed in one package.
- · Excellent in thermal equilibrium and pair capability.

Electrical Connection



Package Dimensions

unit:mm



FC120

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		25	V
Collector-to-Emitter Voltage	VCEO		20	V
Emitter-to-Base Voltage	VEBO		3	V
Collector Current	Ι _C		30	mA
Collector Dissipation	PC	1 unit	200	mW
Total Power Dissipation	PT		300	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to+150	°C

Electrical Characteristics at Ta = 25°C

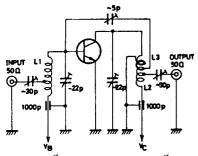
Parameter	Symbol	Conditions	Ratings			Unit
Falanielei			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =10V, I _E =0			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =3V, I _C =0			0.1	μΑ
DC Current Gain	hFE	V _{CE} =6V, I _C =1mA	80		200	
DC Current Gain Ratio	h _{FE} (small/ large)	V _{CE} =6V, I _C =1mA	0.8	0.98		
Base to Emitter Voltage Drop	V _{BE} (large -small)	V _{CE} =6V, I _C =1mA		1.0	15	mV
Gain-Bandwidth Product	fT	V _{CE} =6V, I _C =4mA	450	750		MHz
Reverse Transfer Capacitance	Cre	V _{CE} =6V, f=1MHz		0.6	0.9	pF
Base to Collector Time Constant	r _{bb} 'c _c	V _{CE} =6V, I _C =1mA, f=31.9MHz			19	ps
Noise Figure	NF	V _{CE} =6V, I _C =1mA, f=100MHz		2.2		dB
Power Gain	PG	V _{CE} =6V, I _C =1mA, f=100MHz		28		dB

Note: The specifications shown above are for each individual transistor.

Marking:120

SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

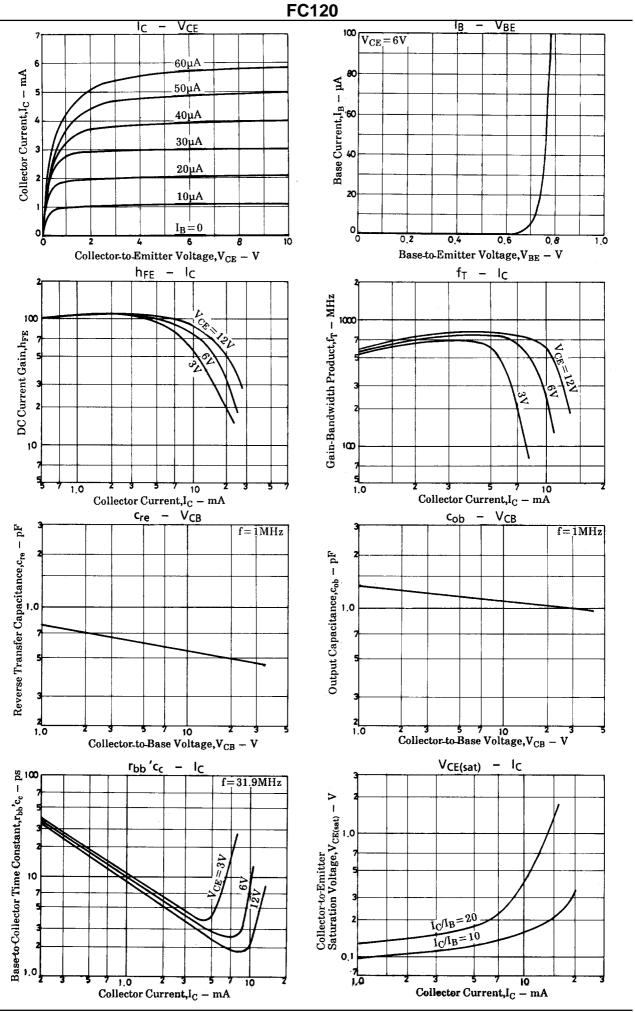


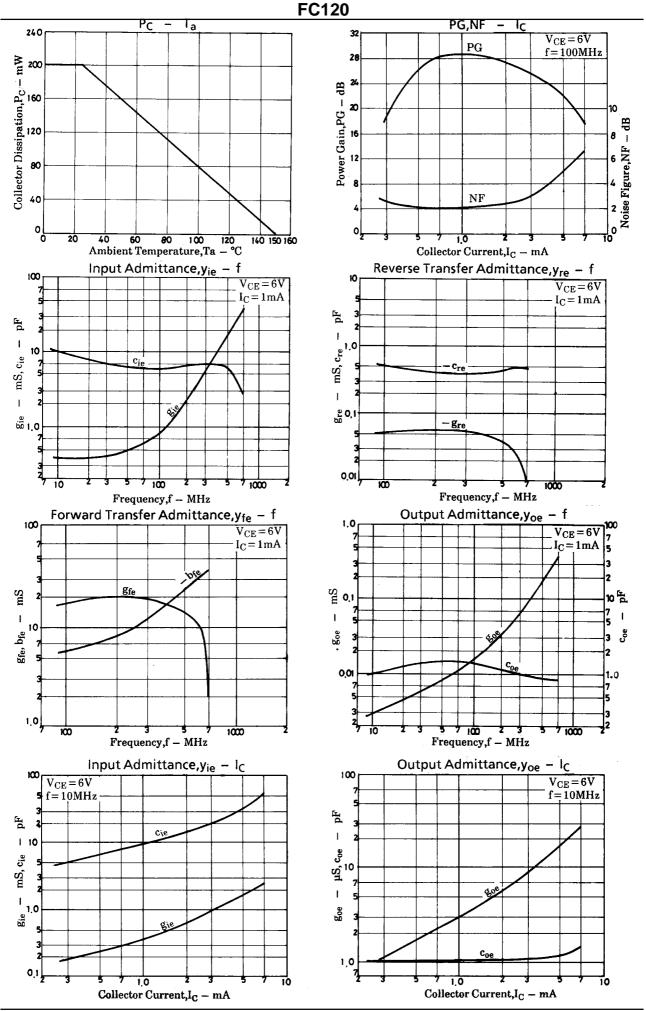


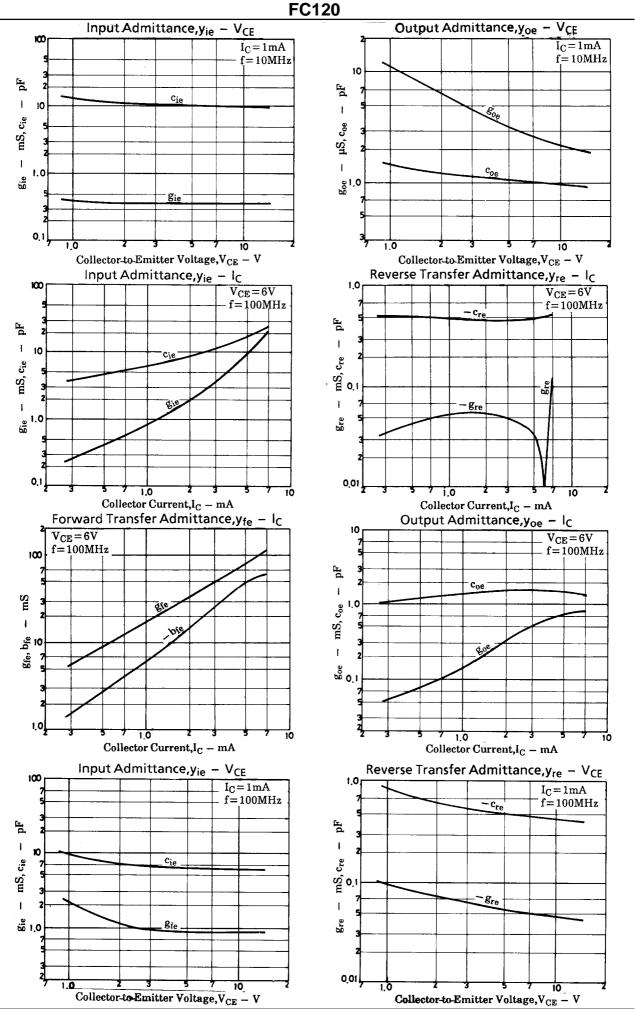
L₁:1mm^Ø plated wire, 10mm^Ø 5T, 15mm pitch, tap : 2T from base side L₂:1mm^Ø plated wire, 10mm^Ø 7T, 10mm pitch, tap : 2T from V_C side

L₃:1mm^ø enamel wire, 10mm^ø 3T, 10mm pitch

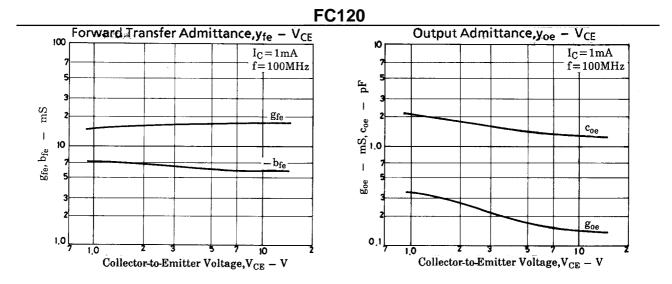
Unit (Capacitance:F)







No.3062-5/6



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